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### IN THE CLAIMS

Please amend claims 2, 7, 16, and 22 as follows below.

Please add new claim 40 as follows below.

The following listing of claims replaces all prior versions, and listings, of claims in the application:

## MARKED UP VERSION OF CLAIMS

1	1. (Cancelled)
1	2. (Currently Amended) An integrated circuit to
2	interface to memory, the integrated circuit comprising
3 .	a first off chip driver calibration terminal to
4	couple to an external pull-up resistor;
5	a first tristate driver having an output coupled
6	to the first off chip driver calibration terminal for
7	pull-up calibration of pull-up transistors;
8	a second off chip driver calibration terminal to
9	couple to an external pull-down resistor;
0	a second tristate driver having an output coupled
11	to the second off chip driver calibration terminal for
12	pull-down calibration of pull-down transistors;

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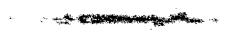
a first switch coupled between the first off chip 13 driver calibration terminal and a voltage reference 14 node; and 15 a second switch coupled between the second off 16 chip driver calibration terminal and the voltage 17 reference node. [[;]] 18 wherein the first switch and the second switch are 19 selectively closed to generate an internal voltage 20 reference on the voltage-reference node with which an 21 input signal is compared in order to receive data. 22 The integrated circuit of claim 2, 3. (Original) 1 2 wherein the first switch is selectively closed and the 3 second switch is selectively opened to generate a pull-4 up calibration voltage on the voltage reference node to 5 calibrate an off-chip driver. The integrated circuit of claim 3, 1 4. (Original) 2 wherein the first switch is selectively opened and the 3 second switch is selectively closed to generate a pull-4 down calibration voltage on the voltage reference node 5 to further calibrate the off-chip driver.

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1	<ol><li>(Previously Presented) An integrated circuit to</li></ol>
2	interface to memory, the integrated circuit comprising:
3	a first off chip driver calibration terminal to
4	couple to an external pull-up resistor;
5	a second off chip driver calibration terminal to
6	couple to an external pull-down resistor;
7	a first switch coupled between the first off chip
8	driver calibration terminal and a voltage reference
9	node;
10	a second switch coupled between the second off
11	chip driver calibration terminal and the voltage
12	reference node; and
13	a plurality of input receivers each having a first
14	input coupled to the voltage reference node and a
15	second input coupled to a respective data terminal of a
16	plurality of data terminals.
1	6. (Original) The integrated circuit of claim 5,
2	wherein
3	each input receiver includes
4	a comparator having a first input coupled to the
5	voltage reference node and a second input coupled to
6	the respective data terminal, the data terminal to
7	couple to an off-chip output driver for calibration.

1	7. (Currently Amended) An integrated caretic to
2	interface to memory, the integrated circuit comprising:
3	a first off chip driver calibration terminal to
4	couple to an external pull-up resistor;
5	a first tristate driver having an output coupled
6	to the first off chip driver calibration terminal for
7	pull-up calibration of pull-up transistors;
8	a second off chip driver calibration terminal to
9	couple to an external pull-down resistor;
10	a second tristate driver having an output coupled
11	to the second off chip driver calibration terminal for
12	pull-down calibration of pull-down transistors;
13	a first switch coupled between the first off chip
14	driver calibration terminal and a voltage reference
15	node;
16	a second switch coupled between the second off
17	chip driver calibration terminal and the voltage
18	reference node; and
19	a switch controller having a mode input, a first
20	control output coupled to a control input of the first
21	switch, and a second control output coupled to a
22	control input of the second switch, the switch
23	controller to control the opening and closing of the
24	first switch and the second switch in response to the
25	mode input.



1	8. (Previously Presented) The integrated circuit of
2	claim 7, wherein
3	the first switch and the second switch are
4	selectively closed to generate an internal voltage
5	reference on the voltage reference node with which an
6	input signal is compared in order to receive data;
7	the first switch is selectively closed and the
8	second switch is selectively opened to generate a pull-
9	up calibration voltage on the voltage reference node to
10	calibrate an off-chip driver; and
11	the first switch is selectively opened and the
12 .	second switch is selectively closed to generate a pull-
13	down calibration voltage on the voltage reference node
14	to further calibrate the off-chip driver.
1	9. (Previously Presented) The integrated circuit of
2	claim 2, wherein
3	the integrated circuit is a memory controller.
1	10. (Previously Presented) The integrated circuit of
2	claim 2, wherein
3	the integrated circuit is a processor.
1	11. (Original) A method in an integrated circuit
2	for interfacing to a memory, the method comprising:

3	if in an off-chip driver calibration mode for a
4	pull-up, then
5	selecting a pull-up calibration terminal to
6	be coupled to a voltage reference node to provide
7	a pull-up calibration voltage thereon, and
8	calibrating a pull-up of an off chip driver;
9	if in an off-chip driver calibration mode for a
10	pull-down, then
11	selecting a pull-down calibration terminal to
12	be coupled to the voltage reference node to
13	provide a pull-down calibration voltage thereon,
14	and
15	calibrating a pull-down of the off chip
16	driver;
17	and,
18	if in a normal mode to receive data, then
19	selecting the pull-up calibration terminal
20	and the pull-down calibration terminal to be
21	coupled to the voltage reference node to provide a
22	reference voltage thereon, and
23	receiving data from a data terminal.
1	12. (Original) The method of claim 11 further
2	comprising:
3	prior to selecting, calibrating and receiving,

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4	coupling an external pull-up resistor to the
5	pull-up calibration terminal; and
6	coupling an external pull-down resistor to
7	the pull-down calibration terminal.
1	13. (Original) The method of claim ll, wherein
2	the receiving data from the data terminal includes
3	comparing the reference voltage on the voltage
4	reference node with an incoming signal on the data
5	terminal.
1	14. (Original) The method of claim 13, wherein
2	the calibrating of the pull-up of the off chip
3	driver includes
4	comparing the pull-up calibration voltage on the
5	voltage reference node with an incoming signal on the
6	data terminal.
1	15. (Original) The method of claim 14, wherein
2	the calibrating of the pull-down of the off chip
3	driver includes
4	comparing the pull-down calibration voltage on the
5	voltage reference node with an incoming signal on the
6	data terminal.
1	16. (Currently Amended) A system comprising:

2	a processor for executing instructions and
3	processing data;
4	a double data rate memory device to store data
5	from the processor and to read data to the processor;
6	an external pull-up resistor having a first end
7	coupled to a first power supply terminal;
8	an external pull-down resistor having a first end
9	coupled to a second power supply terminal; and
10	a memory controller coupled between the double
11	data rate memory device and the processor, the memory
12	controller including
13	a pull-up calibration terminal coupled to a
14	second end of the external pull-up resistor,
15	a first tristate driver having an output
16	coupled to the pull-up calibration terminal for
17	pull-up calibration of pull-up transistors in the
18	double data rate memory device,
19	a pull-down calibration terminal coupled to a
20	second end of the external pull-down resistor,
21	a second tristate driver having an output
22	coupled to the pull-down calibration terminal for
23	pull-down calibration of pull-down transistors in
24	the double data rate memory device,
25	a voltage reference node,
26	a first switch having a first switch
27	connection coupled to the pull-up calibration

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28	terminal and a second switch connection coupled to
29	the voltage reference node, and
30	a second switch having a first switch
31	connection coupled to the pull-down calibration
32	terminal and a second switch connection coupled to
33	the voltage reference node.
1	17. (Original) The system of claim 16, wherein
2	the memory controller is an integrated circuit
3	separate from the processor.
1	18. (Original) The system of claim 16, wherein
2	the processor is an integrated circuit and
3	includes the memory controller.
1	19. (Original) The system of claim 16, wherein
2	the memory controller further includes
3	a switch controller having a mode input, a
4	first control output coupled to a control input of
5	the first switch, and a second control output
6	coupled to a control input of the second switch,
7	the switch controller to control the opening and
8	closing of the first switch and the second switch

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in response to the mode input.

20. (Previously Presented) The system of claim 19, 1 2 wherein the first switch and the second switch are 3 selectively closed to generate an internal voltage 4 reference on the voltage reference node with which an 5 input signal is compared in order to receive data; the first switch is selectively closed and the second switch is selectively opened to generate a pull-8 up calibration voltage on the voltage reference node to 9 calibrate a driver of the DDR memory device; and 10 the first switch is selectively opened and the 11 second switch is selectively closed to generate a pull-12 down calibration voltage on the voltage reference node 13 to further calibrate the driver of the DDR memory 14 15 device.

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#### (Cancelled) 21.

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22. (Currently Amended) A processor for a computer 1 system, the processor including: 2 a memory controller to interface to memory, the 3 memory controller having 4 a pull-up calibration terminal to couple to 5 an external pull-up resistor, 6

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7	a first tristate driver having an output
8	coupled to the pull-up calibration terminal for
9	pull-up calibration of pull-up transistors in the
10	double data rate memory device,
11	a pull-down calibration terminal to couple to
12	an external pull-down resistor,
13	a second tristate driver having an output
14	coupled to the pull-down calibration terminal for
15	pull-down calibration of pull-down transistors in
16	the double data rate memory device,
17	a voltage reference node,
18	a first switch coupled between the pull-up
19	calibration terminal and the voltage reference
20	node,
21	a second switch coupled between the pull-down
22	calibration terminal and the voltage reference
23	node, and
24	a switch controller having a mode input, a
25	first control output coupled to a control input of
26	the first switch, and a second control output
27	coupled to a control input of the second switch,
28	the switch controller to control the opening and
29	closing of the first switch and the second switch
30	in response to the mode input.

1	23. (Previously Presented) The processor of claim
2	22, wherein
3	the first switch and the second switch are
4	selectively closed to generate an internal voltage
5	reference on the voltage reference node with which an
6	input signal is compared in order to receive data from
7	a driver of a memory device;
8	the first switch is selectively closed and the
9	second switch is selectively opened to generate a pull-
10	up calibration voltage on the voltage reference node to
13	calibrate the driver of the memory device; and
12	the first switch is selectively opened and the
13	second switch is selectively closed to generate a pull-
14	down calibration voltage on the voltage reference node
15	to further calibrate the driver of the memory device.
1	24. (Original) A packaged integrated circuit to
2	interface to memory, the packaged integrated circuit
3	comprising:
4	a first off-chip driver calibration terminal to
5	couple to a first external resistor;
6	a second off-chip driver calibration terminal to
7	couple to a second external resistor;
8	a first plurality of field effect transistors
9	having sources coupled in parallel together to the

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- first off-chip driver calibration terminal and drains
  coupled in parallel together to a voltage reference
  node; and
- a second plurality of field effect transistors

  having drains coupled in parallel together to the

  second off-chip driver calibration terminal and sources

  coupled in parallel together to the voltage reference

  node.
  - 1 25. (Original) The packaged integrated circuit of claim 24 wherein
  - the first plurality of field effect transistors
    and the second plurality of field effect transistors
    are p-channel field effect transistors.
  - 1 26. (Original) The packaged integrated circuit of claim 24 wherein
  - the first plurality of field effect transistors

    and the second plurality of field effect transistors

    are n-channel field effect transistors.
  - 1 27. (Original) The packaged integrated circuit of claim 24 wherein
  - 3 the first plurality of field effect transistors
    4 are p-channel field effect transistors, and

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Amdt. Dated 02/06/2005 - MARKET AND THE STREET Reply to Office Action of 11/15/2005 the second plurality of field effect transistors are n-channel field effect transistors. The packaged integrated circuit of 28. (Original) claim 24 wherein the first plurality of field effect transistors are n-channel field effect transistors, and the second plurality of field effect transistors are p-channel field effect transistors. The packaged integrated circuit of 29. (Original) claim 24 wherein the first plurality of field effect transistors are p-channel field effect transistors and n-channel 4

field effect transistors having sources coupled in 5 parallel together and drains coupled in parallel 6 together, and 7 the second plurality of field effect transistors are p-channel field effect transistors and n-channel 9 field effect transistors having sources coupled in 10 parallel together and drains coupled in parallel 11 12 together.

The packaged integrated circuit of 1 30. (Original) claim 24 further comprising: 2

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3	a switch controller having a mode input, a first
4	plurality of switch control signals coupled to
5	respective gates of the first plurality of field effect
6	transistors, a second plurality of switch control
7	signals coupled to respective gates of the second
8	plurality of field effect transistors, the switch
9	controller to control the switching of the first and
10	second plurality of field effect transistors.

- 1 31. (Original) The packaged integrated circuit of claim 24 further comprising:
- a plurality of input receivers each having a first
  input coupled to the voltage reference node and a
  second input coupled to respective data terminals to
  receive data.
- 1 32. (Original) The packaged integrated circuit of claim 31, wherein
- 3 each input receiver includes
- a comparator having a first input coupled to the
  voltage reference node and a second input coupled to a
  respective data terminal to calibrate a pull-up and a
  pull-down of an off-chip output driver.
- 1 33. (Original) The packaged integrated circuit of claim 32, wherein

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3	the comparator of each input receiver further to
4	receive data by comparing a reference voltage on the
5	reference node with an input signal on the respective
6	data terminal.

- 34. (Previously Presented) The integrated circuit of 1 claim 5, further comprising: 2
- a switch controller having a mode input, a first 3 control output coupled to a control input of the first 4 switch, and a second control output coupled to a 5 control input of the second switch, the switch 6 controller to control the opening and closing of the 7 first switch and the second switch in response to the 8 9 mode input.
- (Previously Presented) The integrated circuit of 35. 1 claim 34, wherein 2
  - the first switch and the second switch are selectively closed to generate an internal voltage reference on the voltage reference node with which an input signal is compared in order to receive data;
- the first switch is selectively closed and the 7 second switch is selectively opened to generate a pull-8 up calibration voltage on the voltage reference node to 9 calibrate an off-chip driver; and 10

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the first switch is selectively opened and the 11 second switch is selectively closed to generate a pull-12 down calibration voltage on the voltage reference node 13 to further calibrate the off-chip driver. 14 (Previously Presented) The integrated circuit of 1

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- claim 7. wherein 2 the first switch and the second switch are 3 selectively closed to generate an internal voltage 4 reference on the voltage reference node with which an 5
- (Previously Presented) The integrated circuit of ì 37. claim 7, wherein 2

input signal is compared in order to receive data.

- the first switch is selectively closed and the 3 second switch is selectively opened to generate a pull-4 up calibration voltage on the voltage reference node to 5 calibrate an off-chip driver.
- (Previously Presented) The integrated circuit of 7 38. claim 7, wherein 8
- the first switch is selectively opened and the 9 second switch is selectively closed to generate a pull-10 down calibration voltage on the voltage reference node 11 to calibrate an off-chip driver. 12

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13	39. (Previously Presented) The processor of claim
14	23, wherein
15	the memory device is a double data rate (DDR)
16	memory device.
1	40. (New) The integrated circuit of claim 2,
2	wherein
3	the first switch and the second switch are
4	selectively closed to generate an internal voltage
5	reference on the voltage reference node with which an
6	input signal is compared in order to receive data.

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